

isc Silicon NPN Power Transistor

BU536

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : V_{(BR)CEO} = 480V(Min.)
- High Speed Switching
- High Power Dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

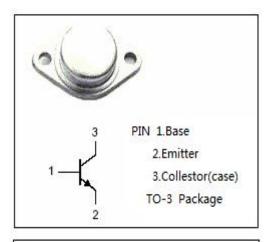
• Designed for use in switching mode power supply.

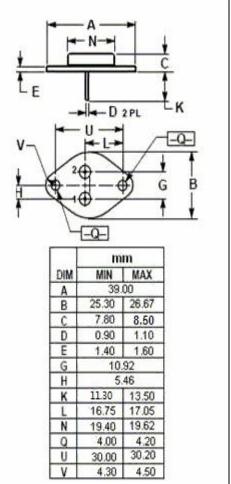
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|-------------------------------------------------------|---------|------|
| V _{CER} | Collector-Emitter Voltage $R_{BE} \approx 100 \Omega$ | 1100 | V |
| V _{CES} | Collector-Emitter Voltage | 1100 | V |
| V _{CEO} | Collector-Emitter Voltage | 480 | V |
| V _{EBO} | Emitter-Base Voltage | 6 | V |
| lc | Collector Current-Continuous | 8 | А |
| Ісм | Collector Current-Peak | 10 | А |
| I _B | Base Current-Continuous | 4 | A |
| Pc | Collector Power Dissipation @ T_c =25°C | 62 | W |
| TJ | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature Range | -65~150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|---------------------|--------------------------------------|-----|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 2.0 | °C/W |





isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

 $T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|----------------------------------------------------------------------------------------------------------------------|-----|------|------------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 50mA; I _B =0 | 480 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA; I _C = 0 | 6 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 4A; I _B = 1A | | | 2.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 4A; I _B = 0.8A | | | 1.4 | V |
| I _{CES} | Collector Cutoff Current | V _{CE} = 1100V; V _{BE} = 0; V _{CE} = 1100V; V _{BE} = 0; T _C = 150℃ | | | 1.0 2.0 | mA |
| hfe-1 | DC Current Gain | I _C = 1A; V _{CE} = 5V | 10 | | | |
| h _{FE-2} | DC Current Gain | I _C = 4A; V _{CE} = 5V | 5.5 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = 0.5A; V _{CE} = 10V | | 10 | | MHz |

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